

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Amend C
J. J. J.
1/6/2



Applicants: Halahan, Patrick B.; Siniaguine, Oleg
Assignee: Tru-Si Technologies, Inc.
Title: Semiconductor Structures Having Multiple Conductive Layers In An Opening, And Methods For Fabricating Same
Application No.: 09/941,447 Filing Date: 08/28/2001
Examiner: Thomas, Toniae M. Group Art Unit: 2822
Docket No.: M-9999-1D US

San Jose, California
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SUPPLEMENTAL AMENDMENT

Sir:

Further to the Amendment submitted 20 August 2002, please amend the above patent application as follows:

IN THE CLAIMS

Amend Claims 60 and 63 to read as follows:

--60. (Amended) The method of Claim 1 wherein removing material along the second side of the substrate comprises (a) removing material of the substrate from its second side and (b) removing material of the first conductive layer exposed from the second side of the substrate so as to expose the second conductive layer from the second side of the substrate.

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